## <u>TOSHIBA</u>

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK2824

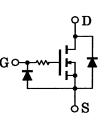
For Portable Equipment High Speed Switch Applications Analog Switch Applications

- High input impedance
- 1.5 V gate drive
- Low gate threshold voltage:  $V_{th} = 0.5 \sim 1.0 \text{ V}$
- Small package

#### Marking

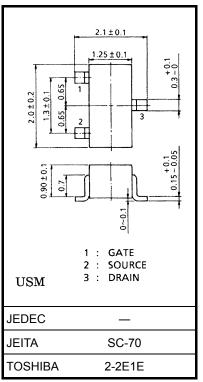
#### **Equivalent Circuit**





#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
DC drain current	ID	100	mA
Drain power dissipation	PD	100	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight: 0.006 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: This transistor is electrostatic sensitive device.

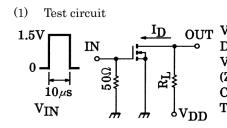
Please handle with caution.

Unit: mm

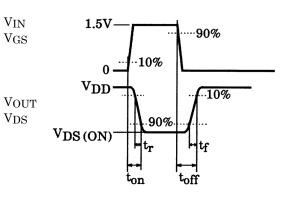
**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_		1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = 20 V, V_{GS} = 0$	_	_	1	μA
Gate threshold vo	ltage	V <sub>th</sub>	$V_{DS} = 1.5 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.5	_	1.0	V
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 1.5 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	35	70	_	mS
Drain-source ON resistance 1		R <sub>DS (ON) 1</sub>	$I_D = 1 \text{ mA}, V_{GS} = 1.2 \text{ V}$		15	50	Ω
Drain-source ON resistance 2		R <sub>DS (ON) 2</sub>	$I_D = 10 \text{ mA}, V_{GS} = 1.5 \text{ V}$		10	40	Ω
Drain-source ON resistance 3		R <sub>DS (ON) 3</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		7	28	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 1.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		12		pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 1.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		3.4		pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 1.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	12		pF
Switching time	Turn-on time	t <sub>on</sub>	V <sub>DD</sub> = 1.5 V, I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0~1.5 V	_	0.35		μs
	Turn-off time	t <sub>off</sub>			0.2		

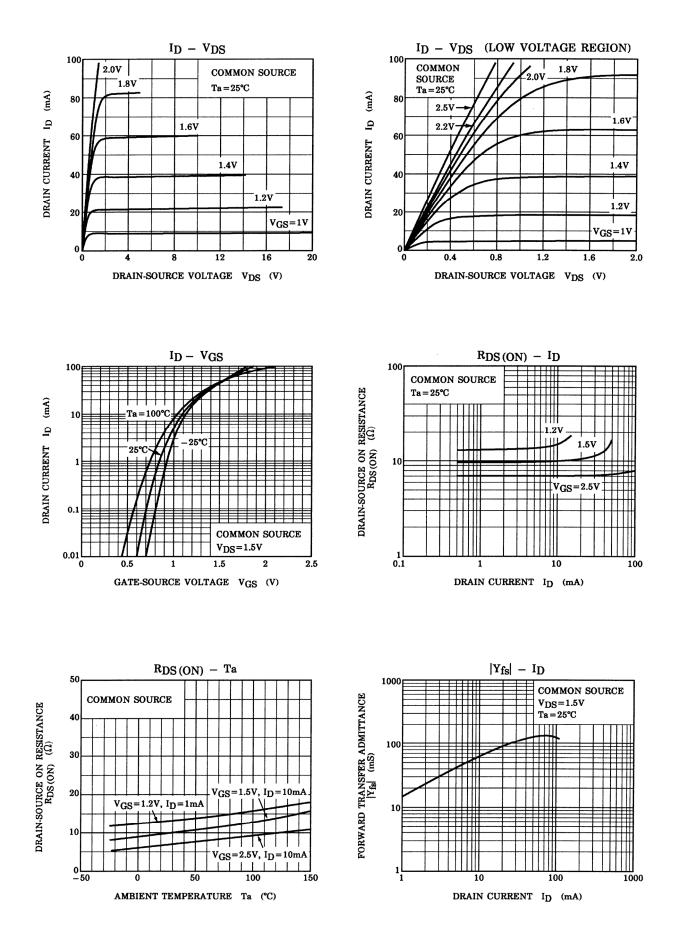
### Switching Time Test Circuit



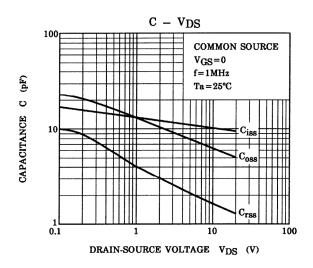
 $(2) V_{IN}$   $V_{DD}=1.5V V_{GS}$   $D.U. \leq 1\%$   $V_{IN}: t_r, t_f < 5ns$   $(Z_{out}=50\Omega)$   $COMMON SOURCE (3) V_{OU}$   $V_{DS}$ 

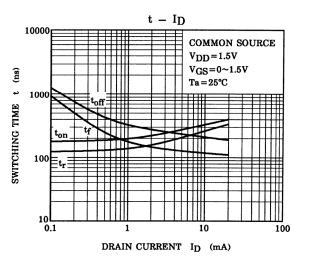


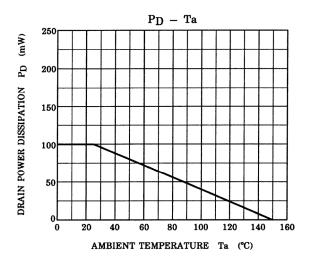
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